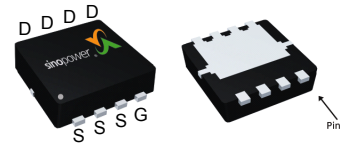


## N-Channel Enhancement Mode MOSFET

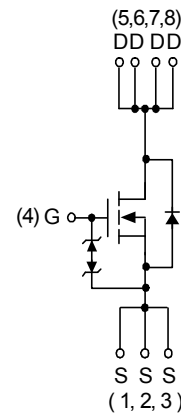
### Features

- 40V/43A,  
 $R_{DS(ON)} = 9.5m\Omega(max.) @ V_{GS} = 10V$   
 $R_{DS(ON)} = 13.5m\Omega(max.) @ V_{GS} = 4.5V$
- ESD protection
- Lower  $Q_g$  and  $Q_{gd}$  for high-speed switching
- Lead Free and Green Devices Available (RoHS Compliant)

### Pin Description



DFN3.3x3.3A-8\_EP

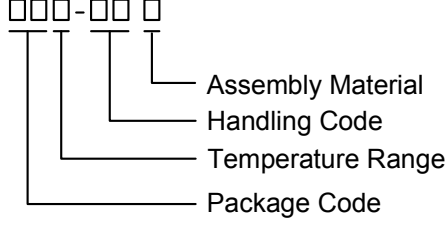


N-Channel MOSFET

### Applications

- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems.

### Ordering and Marking Information

<p>SM3439NH □□□-□□ □</p>  <p>Assembly Material          Handling Code          Temperature Range          Package Code</p>	<p>Package Code          QA : DFN3.3x3.3A-8_EP          Operating Junction Temperature Range          C : -55 to 150 °C          Handling Code          TR : Tape &amp; Reel          Assembly Material          G : Halogen and Lead Free Device</p>
<p>SM3439NH QA : <span style="border: 1px solid black; padding: 2px;">SM 3439N XXXXX</span></p>	<p>XXXXX - Lot Code</p>

Note : SINOPOWER lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. SINOPOWER lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020D for MSL classification at lead-free peak reflow temperature. SINOPOWER defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

SINOPOWER reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

## Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Rating	Unit
<b>Common Ratings</b>			
$V_{DSS}$	Drain-Source Voltage	40	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	
$T_J$	Maximum Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150	
$I_S$	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$ 10	A
$I_D$	Continuous Drain Current	$T_C=25^\circ\text{C}$ 43	
		$T_C=100^\circ\text{C}$ 28	
$I_{DM}$	Pulsed Drain Current	$T_C=25^\circ\text{C}$ 60 <sup>a</sup>	
$P_D$	Maximum Power Dissipation	$T_C=25^\circ\text{C}$ 27.8	W
		$T_C=100^\circ\text{C}$ 11.1	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	Steady State 4.5	$^\circ\text{C/W}$
$I_D$	Continuous Drain Current	$T_A=25^\circ\text{C}$ 12	A
		$T_A=70^\circ\text{C}$ 9.6	
$P_D$	Maximum Power Dissipation	$T_A=25^\circ\text{C}$ 2.08	W
		$T_A=70^\circ\text{C}$ 1.3	
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	$t \leq 10\text{s}$ 40	$^\circ\text{C/W}$
		Steady State <sup>b</sup> 60	
$I_{AS}^c$	Avalanche Current, Single pulse	$L=0.1\text{mH}$ 19	A
$E_{AS}^c$	Avalanche Energy, Single pulse	$L=0.1\text{mH}$ 18	mJ

Note a : Pulse width is limited by maximum junction temperature.

Note b :  $R_{\theta JA}$  steady state  $t=100\text{s}$ .  $R_{\theta JA}$  is measured with the device mounted on  $1\text{in}^2$ , FR-4 board with 2oz. Copper.

Note c : UIS tested and pulse width is limited by maximum junction temperature  $150^\circ\text{C}$  (initial temperature  $T_J = 25^\circ\text{C}$ ).

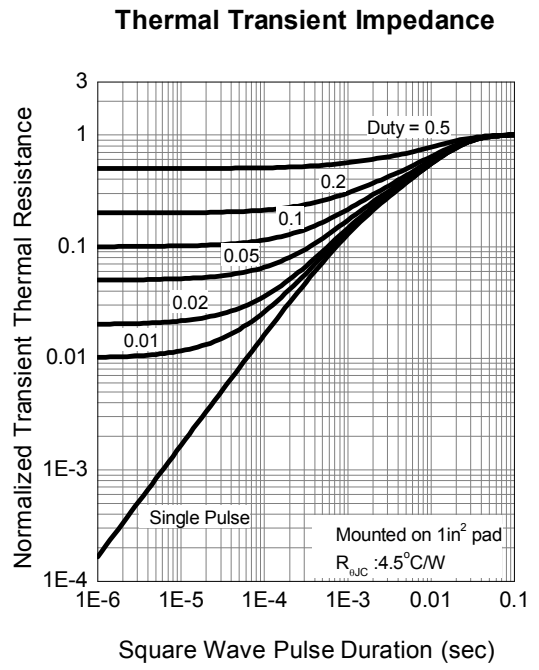
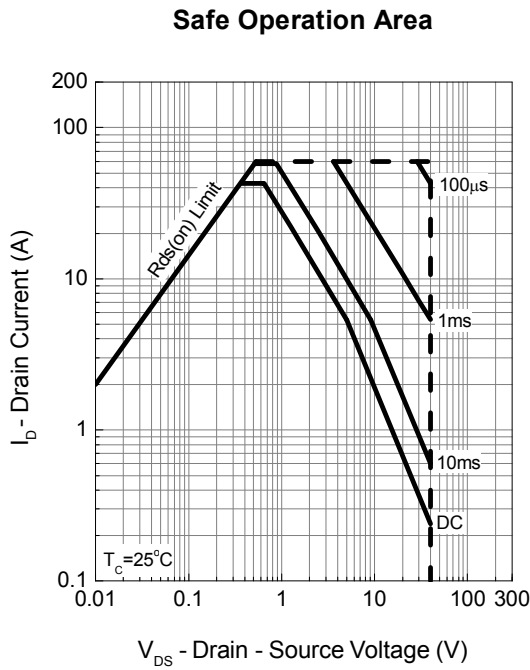
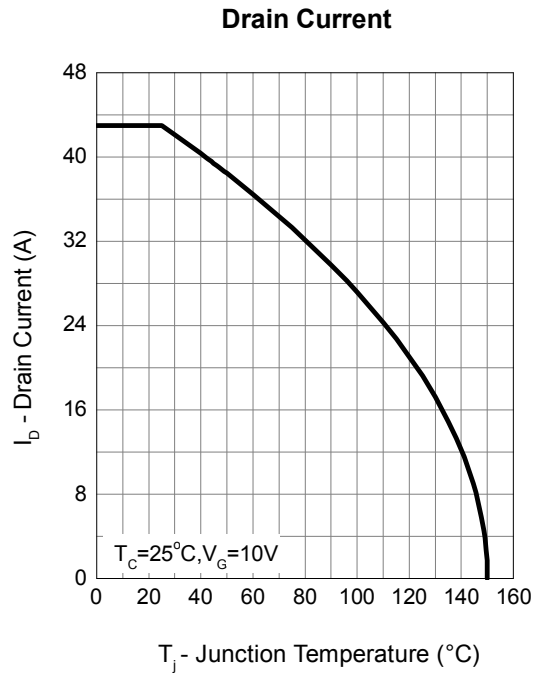
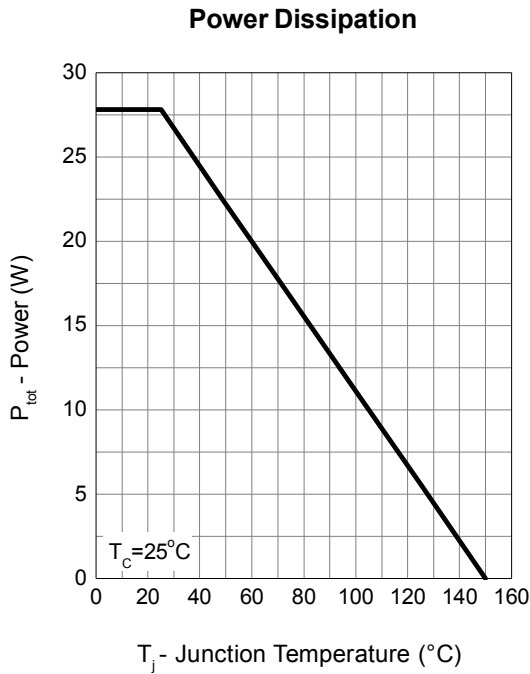
## Electrical Characteristics (T<sub>A</sub> = 25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>DS</sub> =250μA	40	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =32V, V <sub>GS</sub> =0V T <sub>J</sub> =85°C	-	-	1 30	μA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =250μA	1.4	1.8	2.5	V
I <sub>GSS</sub>	Gate Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±10	μA
R <sub>DS(ON)</sub> <sup>d</sup>	Drain-Source On-state Resistance	V <sub>GS</sub> =10V, I <sub>DS</sub> =15A T <sub>J</sub> =125°C	-	7.9 11.8	9.5 -	mΩ
		V <sub>GS</sub> =4.5V, I <sub>DS</sub> =8A	-	11.5	13.5	
Gfs	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>DS</sub> =8A	-	18	-	S
<b>Diode Characteristics</b>						
V <sub>SD</sub> <sup>d</sup>	Diode Forward Voltage	I <sub>SD</sub> =10A, V <sub>GS</sub> =0V	-	0.82	1.1	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =5A, dI <sub>SD</sub> /dt=100A/μs	-	18.8	-	ns
t <sub>a</sub>	Charge Time		-	7.4	-	
t <sub>b</sub>	Discharge Time		-	11.4	-	
Q <sub>rr</sub>	Reverse Recovery Charge		-	4.5	-	
<b>Dynamic Characteristics<sup>e</sup></b>						
R <sub>G</sub>	Gate Resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, F=1MHz	-	1.7	-	Ω
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =20V, Frequency=1.0MHz	-	700	-	pF
C <sub>oss</sub>	Output Capacitance		-	191	-	
C <sub>rss</sub>	Reverse Transfer Capacitance		-	30	-	
t <sub>d(ON)</sub>	Turn-on Delay Time	V <sub>DD</sub> =20V, R <sub>L</sub> =20Ω, I <sub>DS</sub> =1A, V <sub>GEN</sub> =10V, R <sub>G</sub> =6Ω	-	10	-	ns
t <sub>r</sub>	Turn-on Rise Time		-	6.6	-	
t <sub>d(OFF)</sub>	Turn-off Delay Time		-	18	-	
t <sub>f</sub>	Turn-off Fall Time		-	12	-	
<b>Gate Charge Characteristics<sup>e</sup></b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =20V, V <sub>GS</sub> =10V, I <sub>DS</sub> =15A	-	10.7	-	nC
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =20V, V <sub>GS</sub> =4.5V, I <sub>DS</sub> =15A	-	5.1	-	
Q <sub>gth</sub>	Threshold Gate Charge		-	1.55	-	
Q <sub>gs</sub>	Gate-Source Charge		-	2.9	-	
Q <sub>gd</sub>	Gate-Drain Charge		-	1.1	-	

Note d : Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.

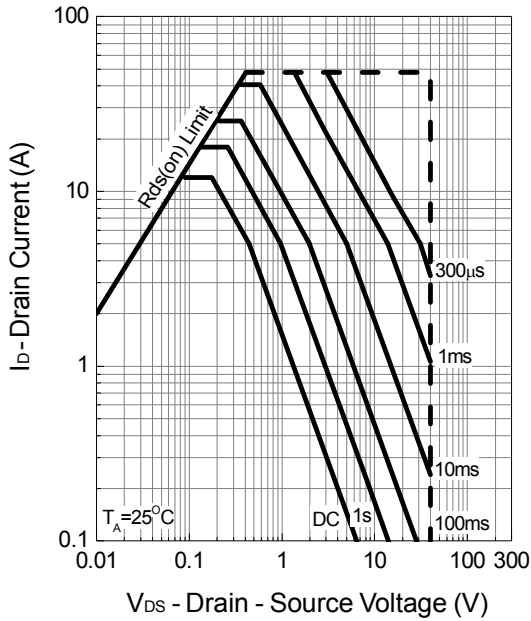
Note e : Guaranteed by design, not subject to production testing.

## Typical Operating Characteristics

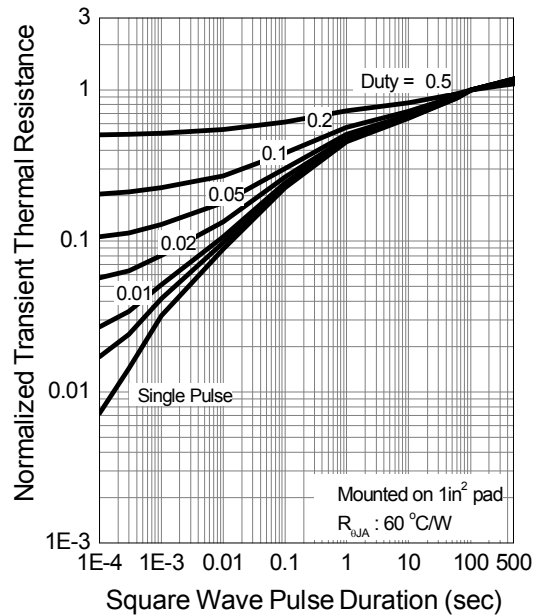


Typical Operating Characteristics (Cont.)

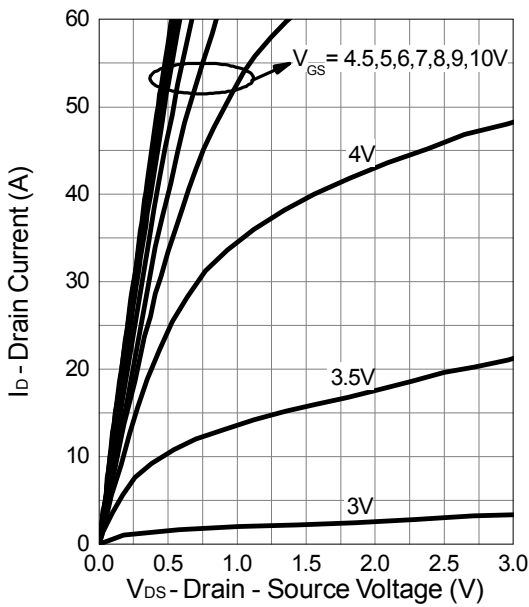
Safe Operation Area



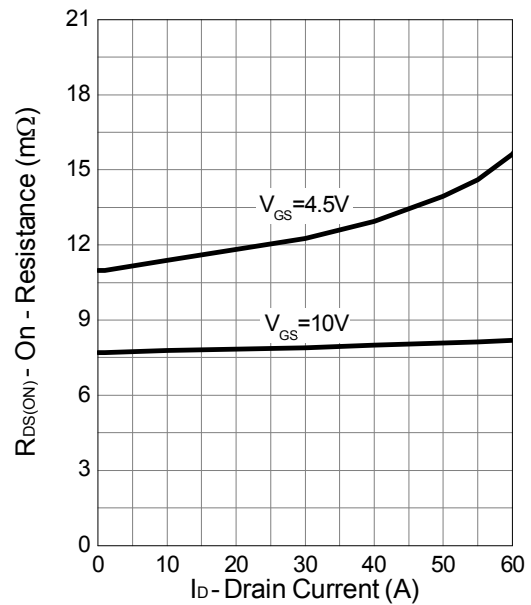
Thermal Transient Impedance



Output Characteristics

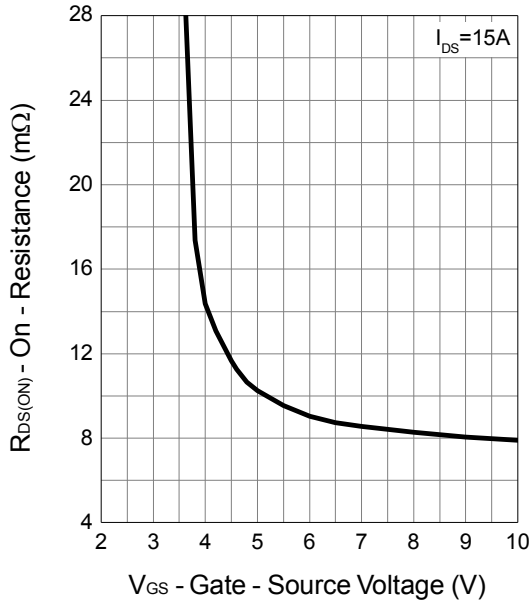


Drain-Source On Resistance

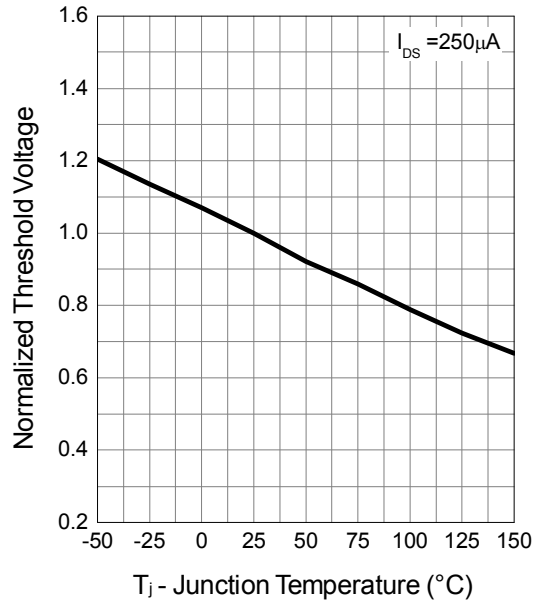


Typical Operating Characteristics (Cont.)

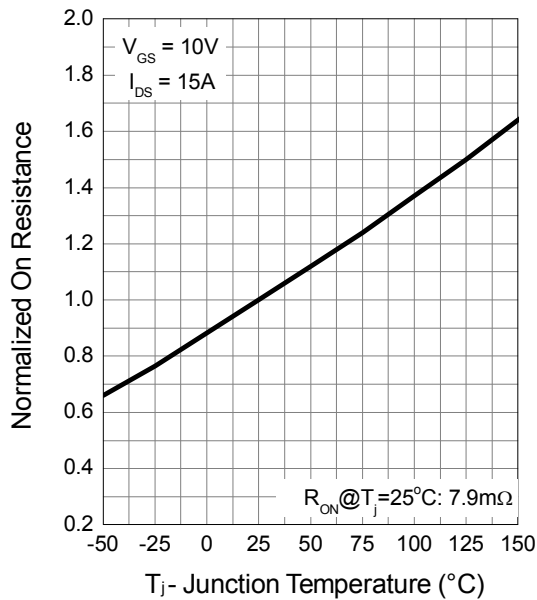
Gate-Source On Resistance



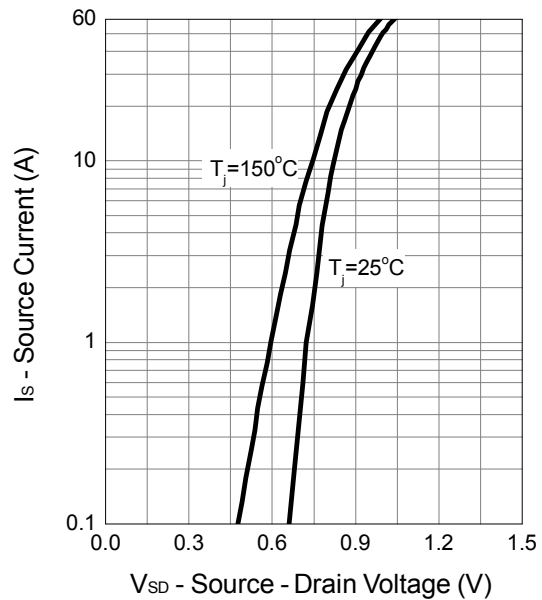
Gate Threshold Voltage



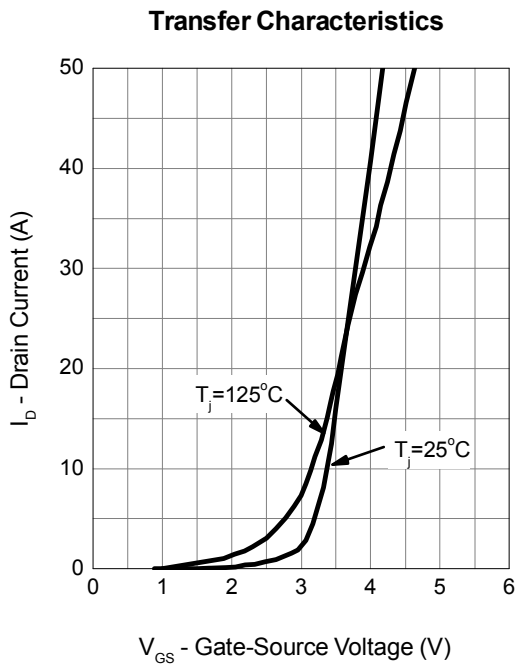
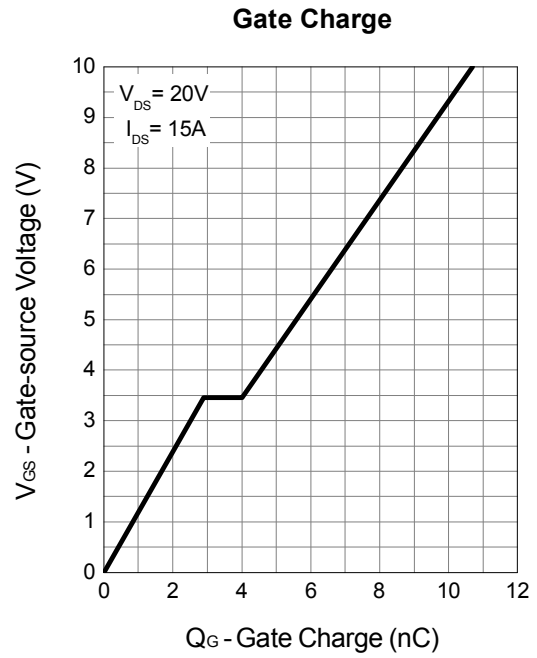
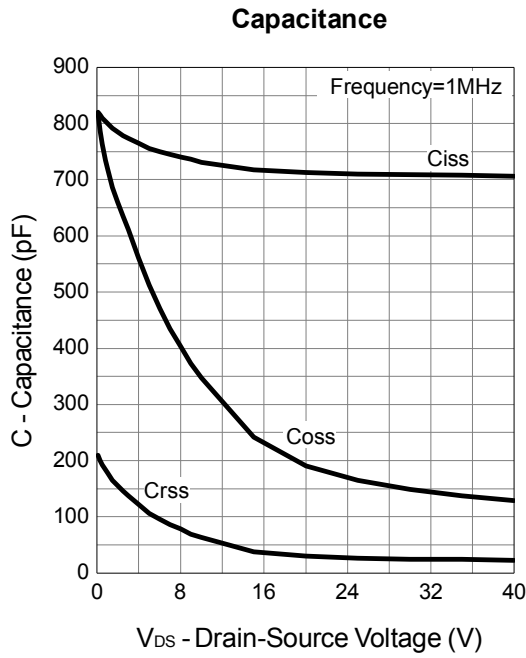
Drain-Source On Resistance



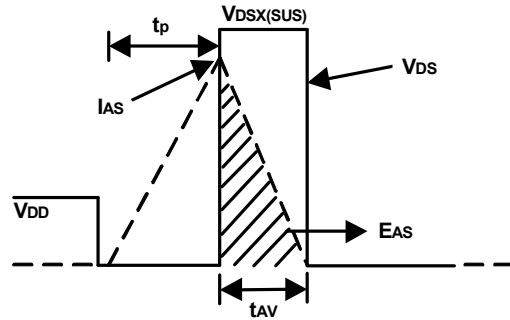
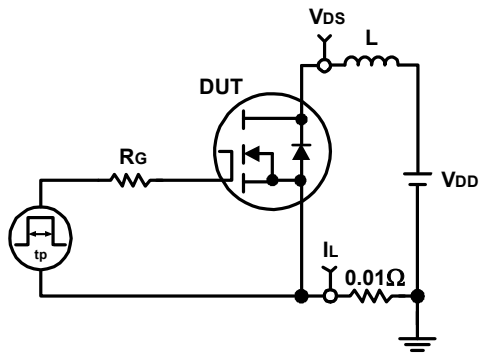
Source-Drain Diode Forward



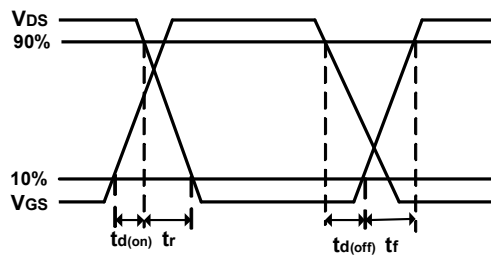
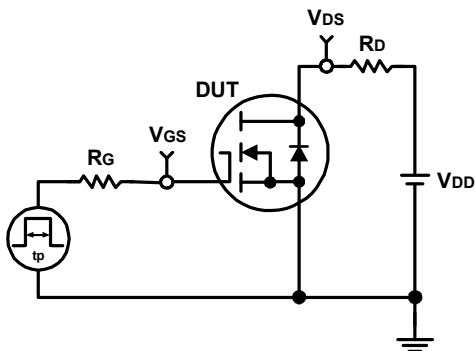
Typical Operating Characteristics (Cont.)



### Avalanche Test Circuit and Waveforms



### Switching Time Test Circuit and Waveforms





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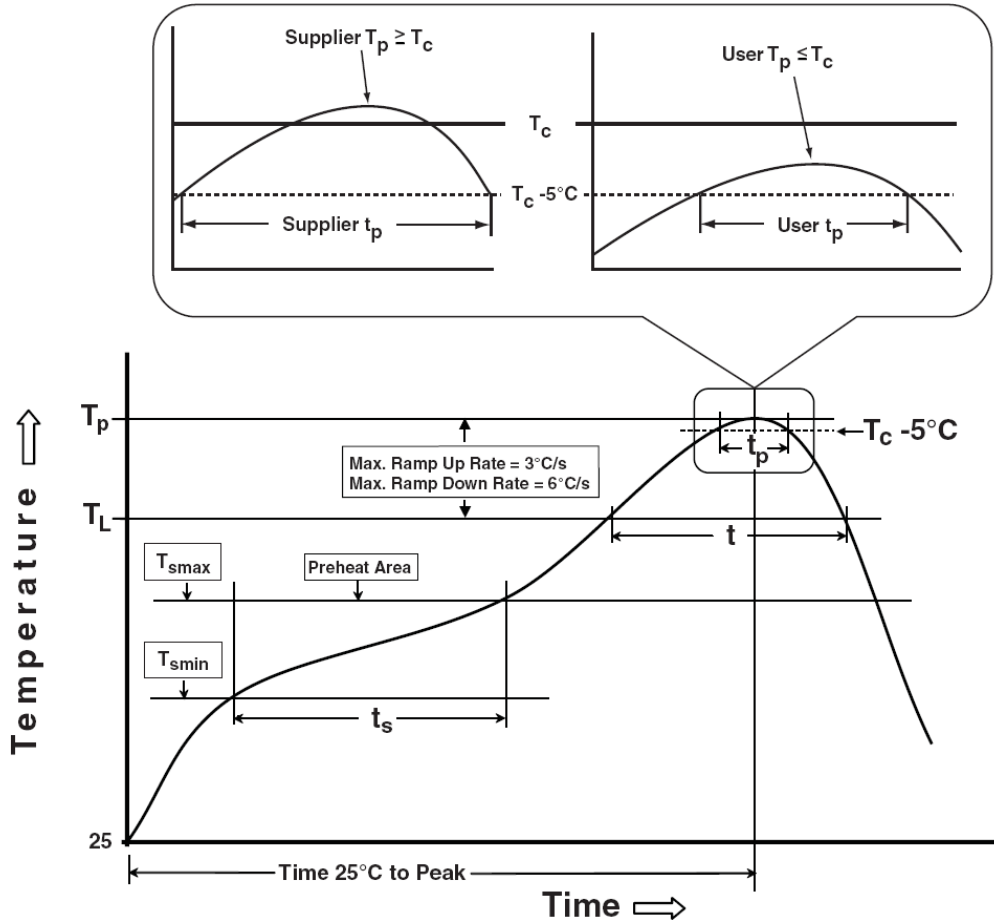
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Classification Profile



## Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
<b>Preheat &amp; Soak</b>		
Temperature min ( $T_{smin}$ )	100 °C	150 °C
Temperature max ( $T_{smax}$ )	150 °C	200 °C
Time ( $T_{smin}$ to $T_{smax}$ ) ( $t_s$ )	60-120 seconds	60-120 seconds
Average ramp-up rate ( $T_{smax}$ to $T_p$ )	3 °C/second max.	3°C/second max.
Liquidous temperature ( $T_L$ )	183 °C	217 °C
Time at liquidous ( $t_L$ )	60-150 seconds	60-150 seconds
Peak package body Temperature ( $T_p$ )*	See Classification Temp in table 1	See Classification Temp in table 2
Time ( $t_p$ )** within 5°C of the specified classification temperature ( $T_c$ )	20** seconds	30** seconds
Average ramp-down rate ( $T_p$ to $T_{smax}$ )	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature ( $T_p$ ) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature ( $t_p$ ) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures ( $T_c$ )

Package Thickness	Volume mm <sup>3</sup> <350	Volume mm <sup>3</sup> ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures ( $T_c$ )

Package Thickness	Volume mm <sup>3</sup> <350	Volume mm <sup>3</sup> 350-2000	Volume mm <sup>3</sup> >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

## Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	1000 Hrs, 80% of VDS max @ Tjmax
HTGB	JESD-22, A108	1000 Hrs, 100% of VGS max @ Tjmax
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C

## Customer Service

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